

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead-free

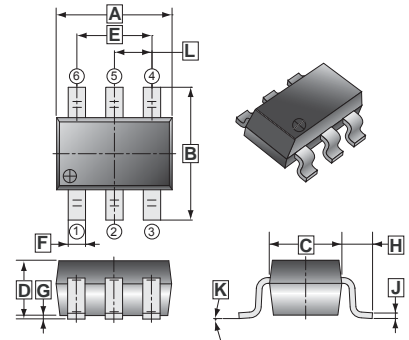
DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density trench process to provide Low $R_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

FEATURES

- Low $R_{DS(on)}$ provides higher efficiency and extends battery life.
- Low thermal impedance copper leadframe TSOP-6 saves board space.
- Fast switching speed
- High performance trench technology

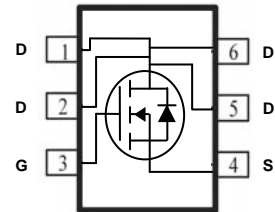
TSOP-6



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	0	0.10
B	2.60	3.00	H	0.60 REF.	
C	1.40	1.80	J	0.12 REF.	
D	1.10 MAX.		K	0°	10°
E	1.90 REF.		L	0.95 REF.	
F	0.30	0.50			

PACKAGE INFORMATION

Package	MPQ	LeaderSize
TSOP-6	3K	7' inch



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ¹	I_D	$T_A=25^\circ\text{C}$	6.0
		$T_A=70^\circ\text{C}$	4.6
Pulsed Drain Current ²	I_{DM}	20	A
Continuous Source Current (Diode Conduction) ¹	I_S	1.6	A
Power Dissipation ¹	P_D	$T_A=25^\circ\text{C}$	2
		$T_A=70^\circ\text{C}$	1.3
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ 150	$^\circ\text{C}$
Thermal Resistance Ratings			
Maximum Junction to Ambient ¹	$R_{\theta JA}$	$t \leq 5 \text{ sec}$	62.5
		Steady State	110

Notes:

1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	0.7	-	1.5	V	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$
Gate-Body Leakage	I_{GSS}	-	-	± 100	nA	$V_{DS}=0\text{V}$, $V_{GS}=\pm 8\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$
		-	-	10		$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$
On-State Drain Current ¹	$I_{D(on)}$	10	-	-	A	$V_{DS}=5\text{V}$, $V_{GS}=4.5\text{V}$
Drain-Source On-Resistance ¹	$R_{DS(ON)}$	-	-	32	m Ω	$V_{GS}=4.5\text{V}$, $I_D=6.0\text{A}$
		-	-	44		$V_{GS}=2.5\text{V}$, $I_D=5.0\text{A}$
Forward Transconductance ¹	g_{fs}	-	11.3	-	S	$V_{DS}=10\text{V}$, $I_D=4.0\text{A}$
Diode Forward Voltage	V_{SD}	-	0.75	-	V	$I_S=1.6\text{A}$, $V_{GS}=0\text{V}$
Dynamic ²						
Total Gate Charge	Q_g	-	6	-	nC	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=4.0\text{A}$
Gate-Source Charge	Q_{gs}	-	1	-		
Gate-Drain Charge	Q_{gd}	-	1.5	-		
Turn-on Delay Time	$T_{d(on)}$	-	8	-	nS	$V_{DD}=10\text{V}$, $V_{GEN}=4.5\text{V}$, $R_L=15\Omega$, $I_D=1\text{A}$
Rise Time	T_r	-	24	-		
Turn-off Delay Time	$T_{d(off)}$	-	35	-		
Fall Time	T_f	-	10	-		

Notes:

1. Pulse test : $PW \leq 300 \mu\text{s}$ duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.